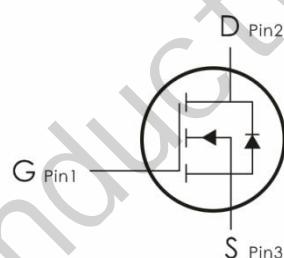


Features:

- Low Intrinsic Capacitances.
- Excellent Switching Characteristics.
- Extended Safe Operating Area.
- Unrivalled Gate Charge : $Q_g=76\text{nC}$ (Typ.).
- $\text{BV}_{\text{DSS}}=80\text{V}, I_{\text{D}}=100\text{A}$
- $R_{\text{DS(on)}} : 8.2\text{m}\Omega$ (Max) @ $V_{\text{G}}=10\text{V}$
- 100% Avalanche Tested


Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Maximum | Unit |
|-----------------------|--------------------------------------|-------------------------|------------------|
| V_{DSS} | Drain-to-Source Voltage | 80 | V |
| V_{GSS} | Gate-to-Source Voltage | ± 25 | V |
| I_{D}^3 | Continuous Drain Current | $T_C=25^\circ\text{C}$ | 100 |
| | | $T_C=100^\circ\text{C}$ | 70 |
| I_{DP}^4 | Pulsed Drain Current | $T_C=25^\circ\text{C}$ | 340 |
| I_{AS}^5 | Avalanche Current | 20 | |
| E_{AS}^5 | Avalanche energy | 410 | mJ |
| PD | Maximum Power Dissipation | $T_C=25^\circ\text{C}$ | 240 |
| | | $T_C=100^\circ\text{C}$ | 100 |
| T_J, T_{STG} | Junction & Storage Temperature Range | -55~175 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Typical | Unit |
|-----------------------|--|---------|--------------------|
| $R_{\theta\text{jc}}$ | Thermal Resistance-Junction to Case | 0.52 | $^\circ\text{C/W}$ |
| $R_{\theta\text{ja}}$ | Thermal Resistance-Junction to Ambient | 55 | |

Electrical Characteristics (TA=25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min. | Typ | Max. | Unit |
|---|----------------------------------|--|------|------|------|------|
| Static Characteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 80 | — | — | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =64V, V _{GS} =0V | — | — | 1 | uA |
| | | T _J =125°C | — | — | 100 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 2 | 3 | 4 | V |
| I _{GSS} | Gate Leakage Current | V _{GS} =±25V, V _{DS} =0V | — | — | ±100 | nA |
| R _{DS(on)} ¹ | Drain-Source On-Resistance | V _{GS} =10V, I _D =40A | — | 7.4 | 8.2 | mΩ |
| | | — | — | — | — | |
| Diode Characteristics | | | | | | |
| V _{SD} ¹ | Diode Forward Voltage | I _{SD} =40A, V _{GS} =0V | — | — | 1.3 | V |
| I _s ³ | Diode Continuous Forward Current | — | — | — | 100 | A |
| t _{rr} | Reverse Recovery Time | I _F =40A, dI/dt=100A/us | — | 25 | — | nS |
| Q _{rr} | Reverse Recovery Charge | | — | 18.5 | — | nC |
| Dynamic Characteristics ² | | | | | | |
| R _G | Gate Resistance | V _{GS} =0V, V _{DS} =0V, Frequency=1MHz | — | 1.3 | — | Ω |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =25V Frequency=1MHz | — | 3850 | — | pF |
| C _{oss} | Output Capacitance | | — | 480 | — | |
| C _{rss} | Reverse Transfer Capacitance | | — | 278 | — | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} =37.5V, I _D =40A, V _{GS} =10V, R _G =6.8Ω | — | 20.4 | — | nS |
| t _r | Rise Time | | — | 63 | — | |
| t _{d(off)} | Turn-Off Delay Time | | — | 67 | — | |
| t _f | Fall Time | | — | 43 | — | |
| Gate Charge Characteristics ² | | | | | | |
| Q _g | Total Gate Charge | V _{DS} =37.5V, V _{GS} =10V I _D =40A | — | 76 | — | nC |
| Q _{gs} | Gate-to-Source Charge | | — | 9.5 | — | |
| Q _{gd} | Gate-to-Drain Charge | | — | 40 | — | |

Note: 1: Pulse test; pulse width \leq 300us, duty cycle \leq 2%.

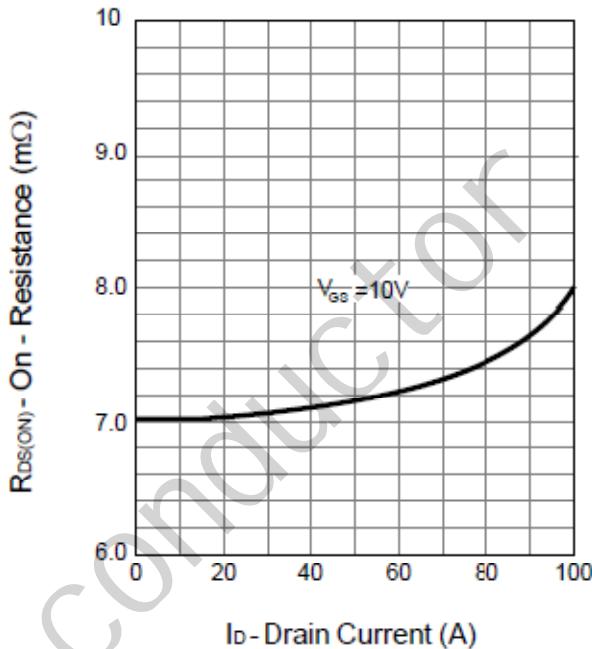
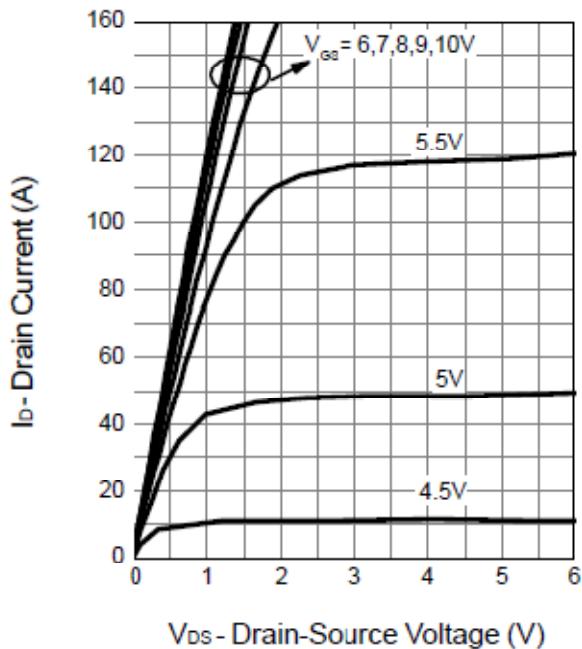
2: Guaranteed by design, not subject to production testing.

3: Package limitation current is 50A.Calculated continuous current based on maximum allowable junction temperature.

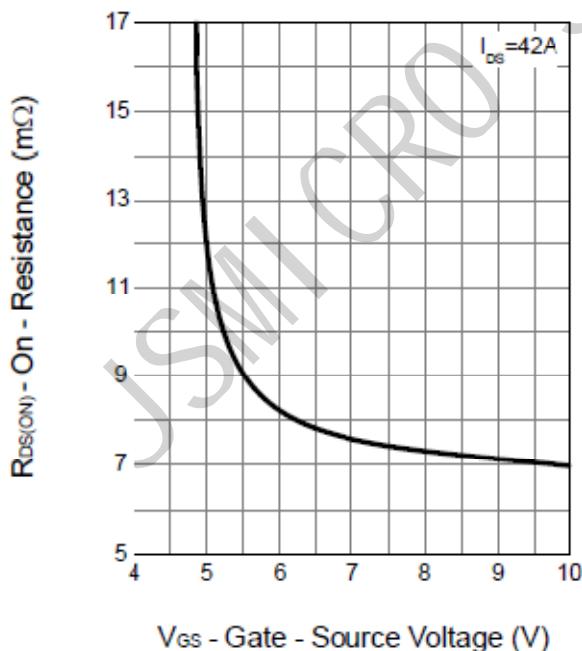
4: Repetitive rating, pulse width limited by max junction temperature.

5: Starting TJ = 25°C,L = 1mH,IAS = 40A.

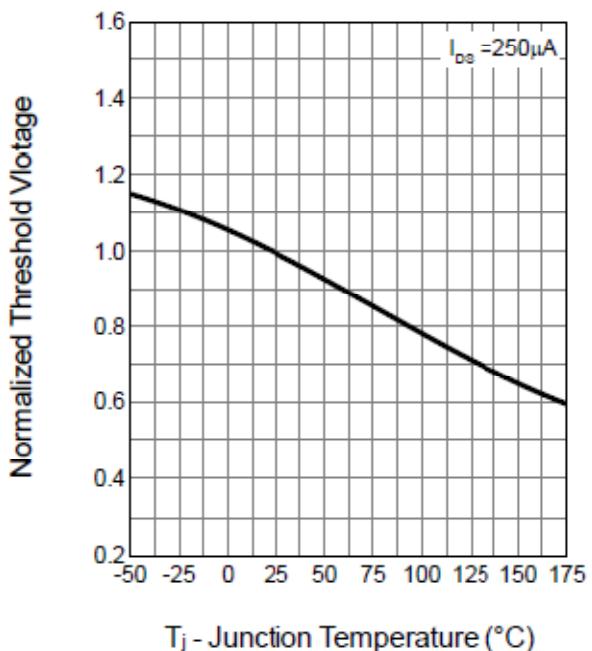
Typical Characteristics

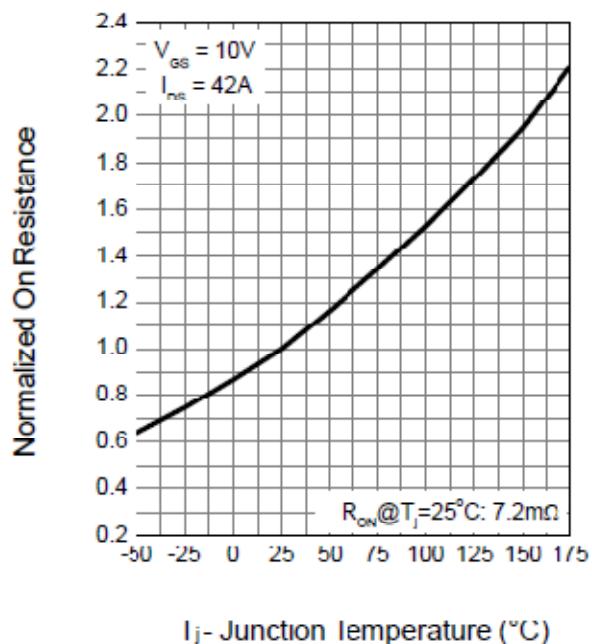
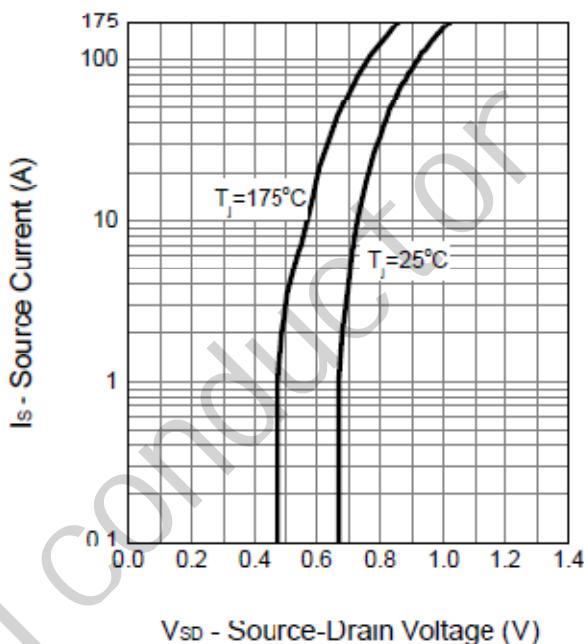
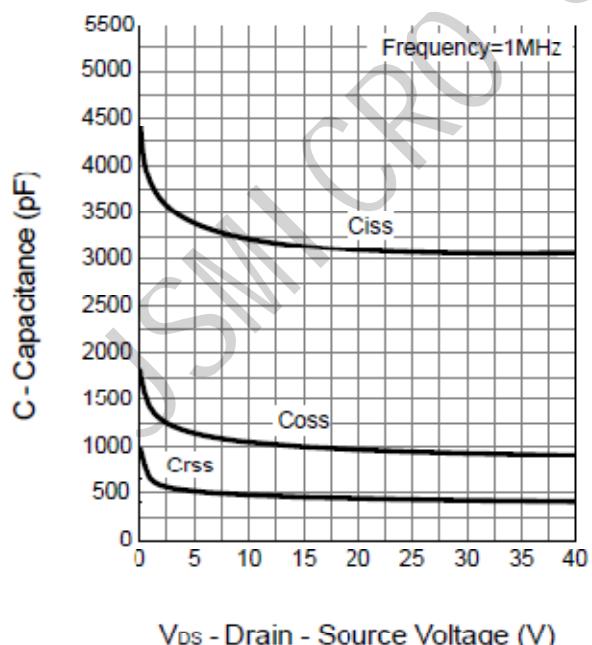
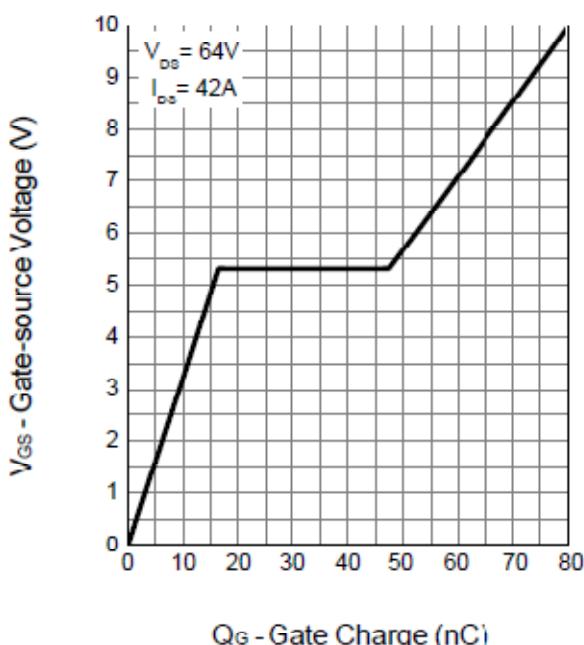


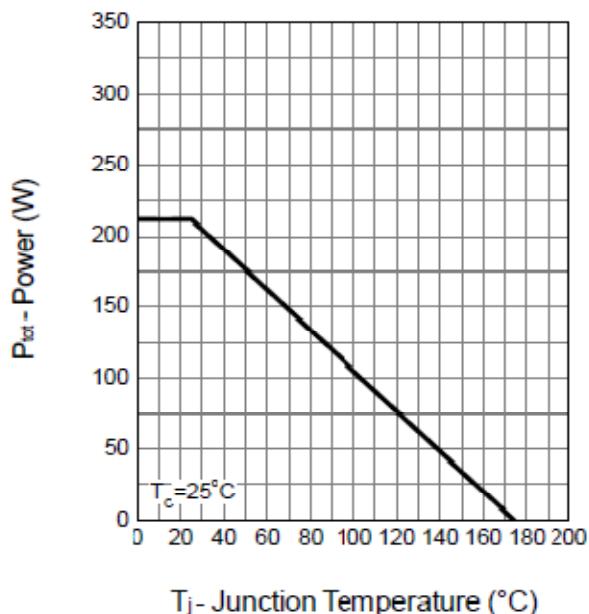
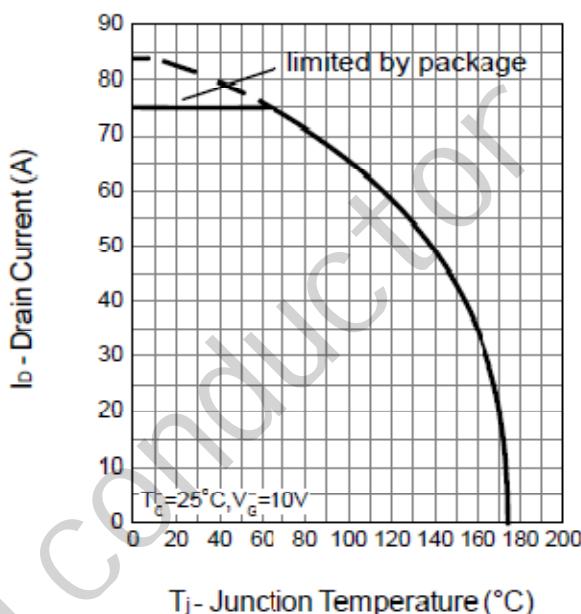
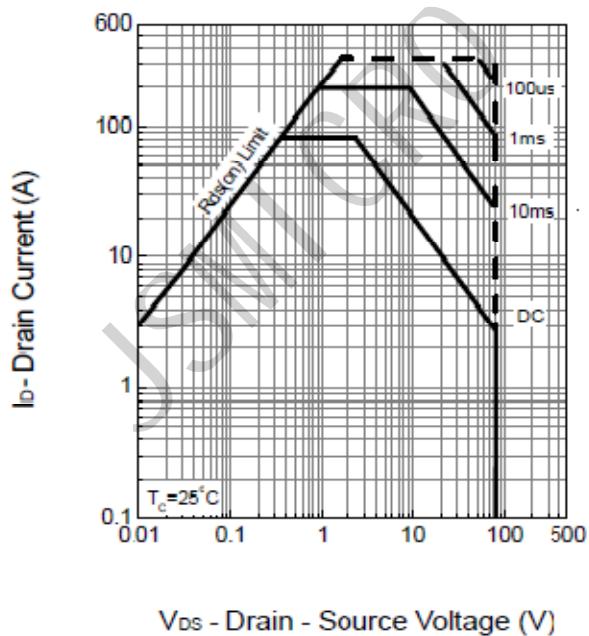
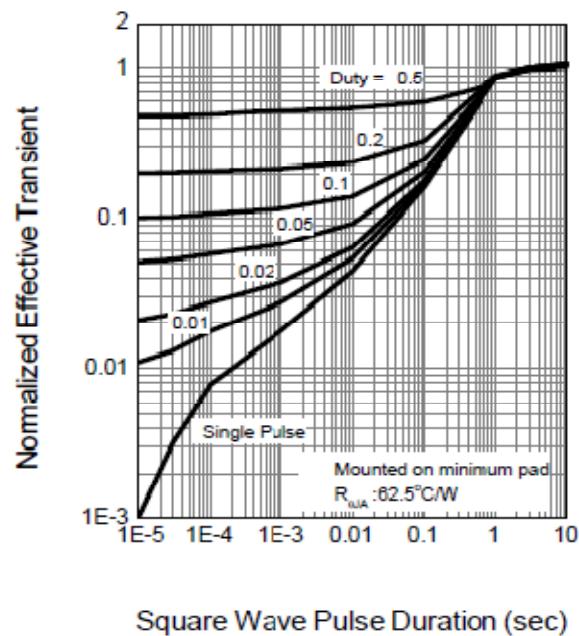
Drain-Source On Resistance



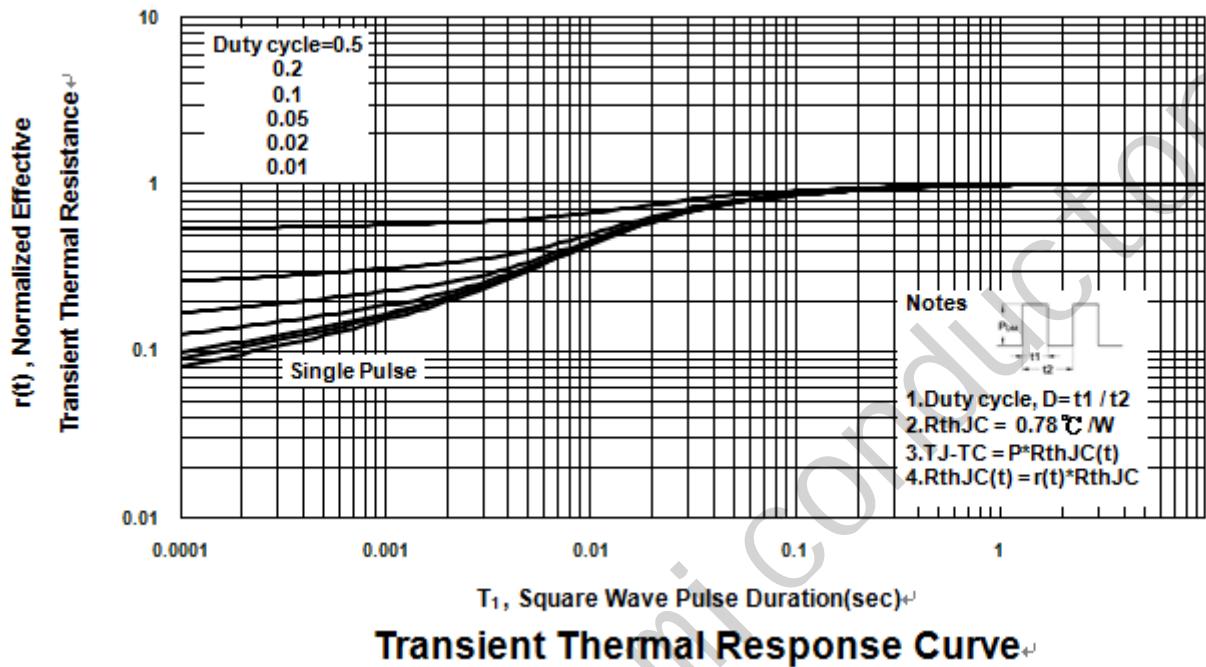
Gate Threshold Voltage



Typical Characteristics (Continued)
Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


Typical Characteristics (Continued)
Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance

 V_{DS} - Drain - Source Voltage (V)

Square Wave Pulse Duration (sec)

Typical Characteristics (Continued)


外形尺寸图 / Package Dimensions

TO-263

Unit: mm

